KSN60N04X

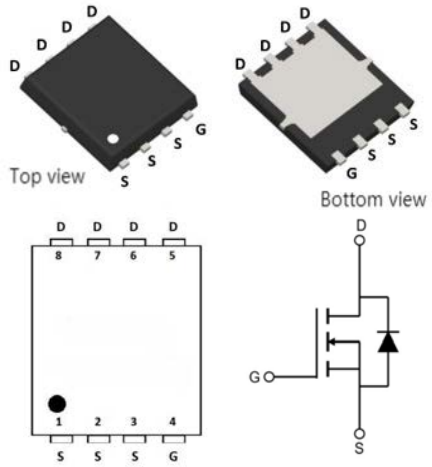
General Description

The KSN60N04X uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V.

40V N-Channel MOSFETs

BVDSS	RDSON	ID
40V	8.0mΩ	70A

PDFN5X6 Pin Configuration



Features

- 40V, 70A, RDS(ON)=8.0mΩ@VGS = 10V
- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

- Notebook
- Load Switch
- LED applications
- Hand-Held Device

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current – Continuous (T_C=25℃)	70	A
	Drain Current – Continuous (T_C=100℃)	44	A
I_{DM}	Drain Current – Pulsed[1]	240	A
EAS	Single Pulse Avalanche Energy[2]	76	mJ
IAS	Single Pulse Avalanche Current[2]	39	A
P_D	Power Dissipation (T_C=25℃)	75.3	W
	Power Dissipation – Derate above 25℃	0.58	W/℃
T_{STG}	Storage Temperature Range	-50 to 150	℃
T_J	Operating Junction Temperature Range	-50 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	1.73	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted) Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	40	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.03	---	V/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=40V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=32V , V_{GS}=0V , T_J=85℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=15A	---	8.0	9.5	mΩ
		V_{GS}=4.5V , I_D=8A	---	9	12	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	1.6	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5	---	mV/℃
gfs	Forward Transconductance	V_{DS}=10V , I_D=10A	---	13	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[3,4]	V_{DS}=20V , V_{GS}=10V , I_D=10A	---	19.7	30	nC
Q_{gs}	Gate-Source Charge[3,4]		---	2.8	4.2	
Q_{gd}	Gate-Drain Charge[3,4]		---	5.1	7.6	
$T_{d(on)}$	Turn-On Delay Time[3,4]	V_{DD}=15V, V_{GS}=10V , R_G=3.3Ω I_D=1A	---	13.2	25	ns
T_r	Rise Time[3,4]		---	2.2	5	
$T_{d(off)}$	Turn-Off Delay Time[3,4]		---	72	130	
T_f	Fall Time[3,4]		---	4.5	10	
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , F=1MHz	---	1578	2200	pF
C_{oss}	Output Capacitance		---	135	250	
C_{rss}	Reverse Transfer Capacitance		---	87	170	
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, F=1MHz	---	2.2	---	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	70	A
I_{SM}	Pulsed Source Current		---	---	140	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1	V
t_{rr}	Reverse Recovery Time	V_{GS}=0V,I_S=1A , dI/dt=100A/μs T_J=25℃	---	17	---	ns
Q_{rr}	Reverse Recovery Charge		---	2.8	---	nC

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=39A.,R_G=25Ω,Starting T_J=25℃.
3. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
4. Essentially independent of operating temperature.

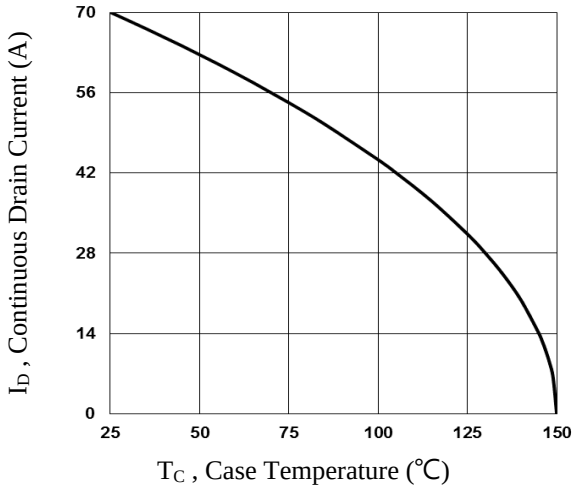


Fig.1 Continuous Drain Current vs. T_C

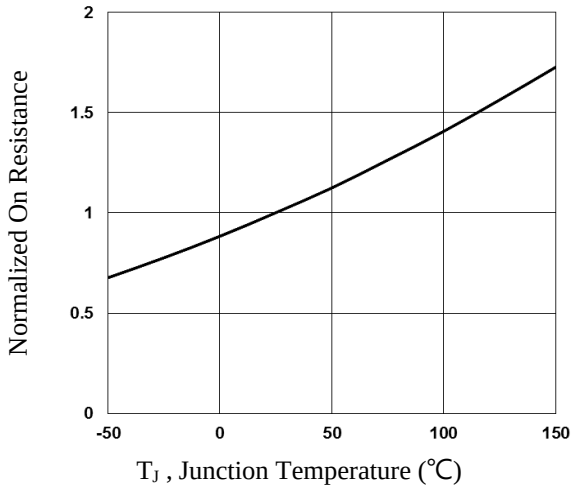


Fig.2 Normalized RDSON vs. T_J

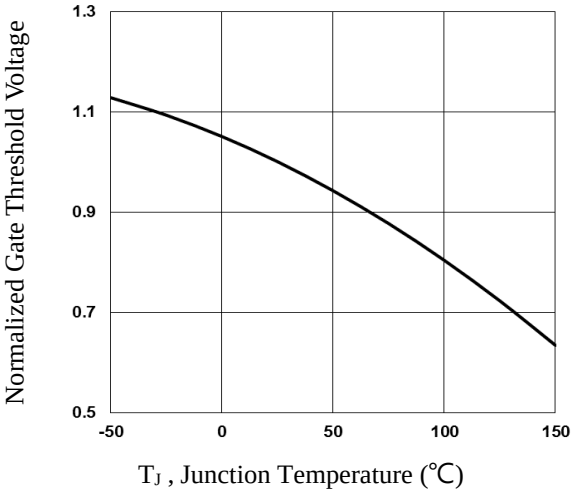


Fig.3 Normalized V_{th} vs. T_J

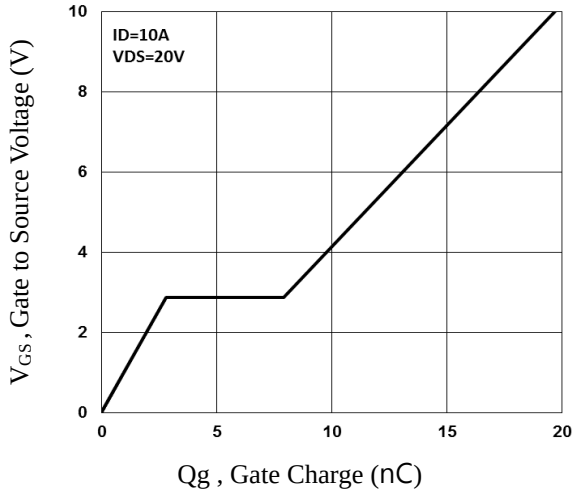


Fig.4 Gate Charge Waveform

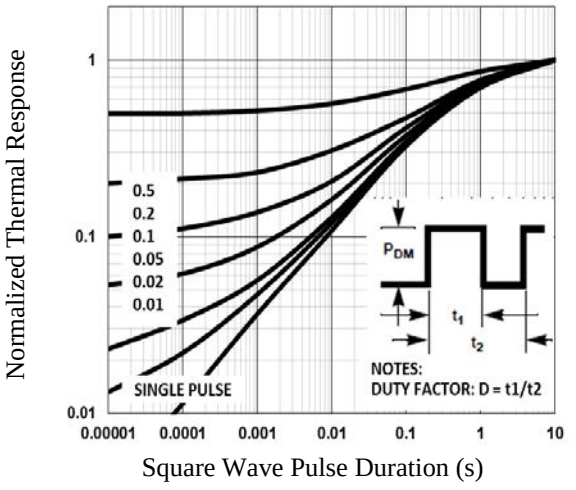


Fig.5 Normalized Transient Impedance

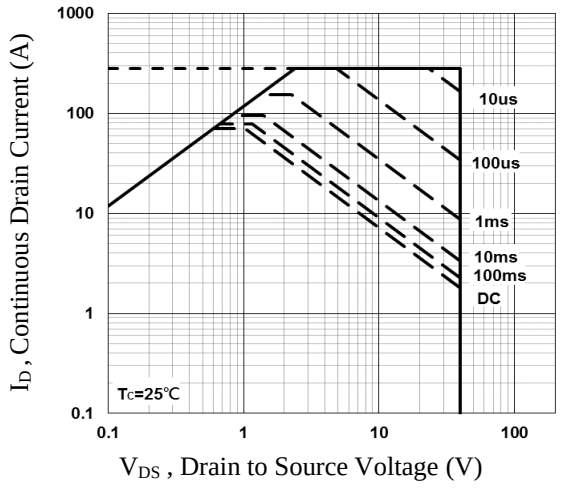


Fig.6 Maximum Safe Operation Area

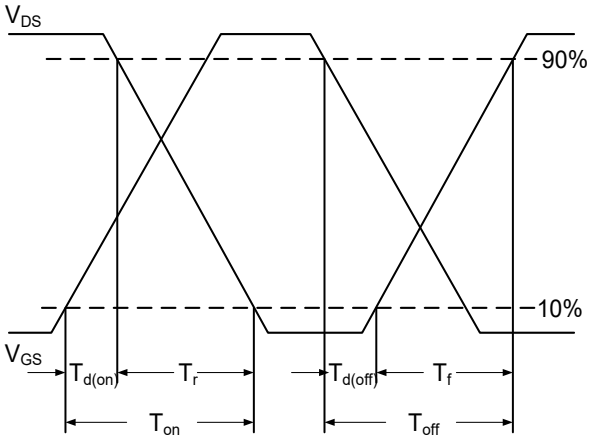


Fig.7 Switching Time Waveform

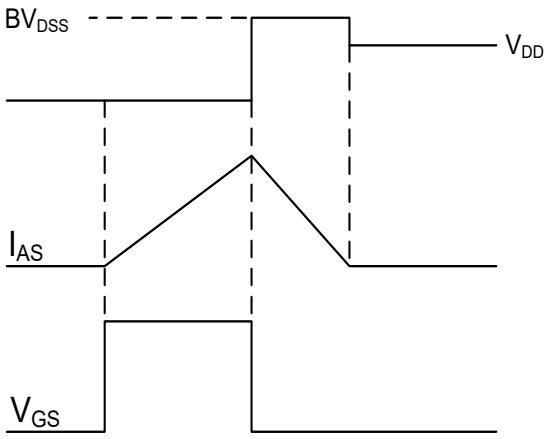
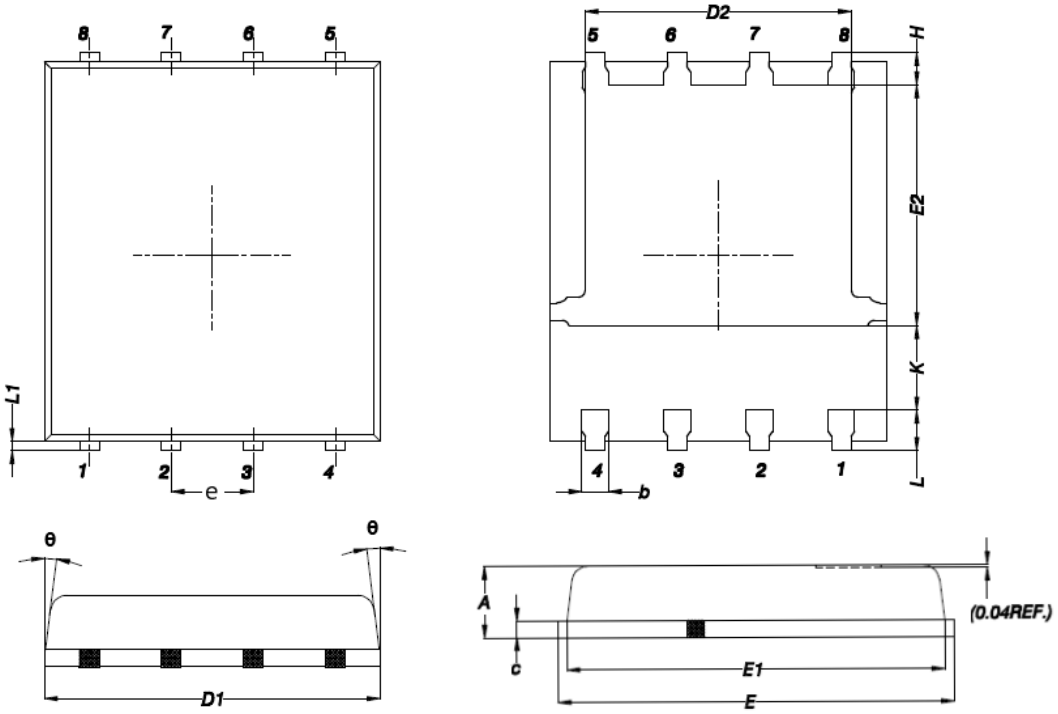


Fig.8 EAS Waveform

MOSFETs PDFN5x6 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.200	0.850	0.047	0.031
b	0.510	0.300	0.020	0.012
C	0.300	0.200	0.012	0.008
D1	5.400	4.800	0.212	0.189
D2	4.310	3.610	0.170	0.142
E	6.300	5.850	0.248	0.230
E1	5.960	5.450	0.235	0.215
E2	3.920	3.300	0.154	0.130
e	1.27BSC		0.05BSC	
H	0.650	0.380	0.026	0.015
K	---	1.100	---	0.043
L	0.710	0.380	0.028	0.015
L1	0.250	0.050	0.009	0.002
θ	12°	0°	12°	0°